

Dual P-Channel 1.8-V (G-S) MOSFET

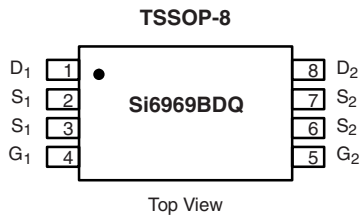
PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 12	0.030 at $V_{GS} = - 4.5$ V	- 4.6
	0.040 at $V_{GS} = - 2.5$ V	- 3.8
	0.055 at $V_{GS} = - 1.8$ V	- 3.0

FEATURES

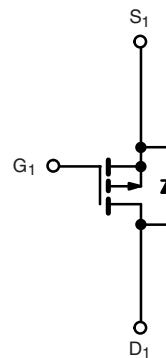
- Halogen-free Option Available
- TrenchFET[®] Power MOSFETs



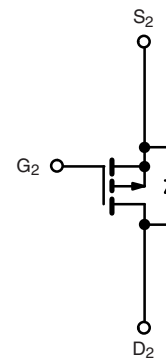
RoHS*
COMPLIANT



Ordering Information: Si6969BDQ-T1
Si6969BDQ-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage	V_{DS}	- 12		V
Gate-Source Voltage	V_{GS}	± 8		
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	- 4.6	- 4.0
		$T_A = 70$ °C	- 3.8	- 3.2
Pulsed Drain Current (10 μ s Pulse Width)	I_{DM}	- 30		A
Continuous Source Current (Diode Conduction) ^a	I_S	- 1.0	- 0.7	
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	1.14	0.83
		$T_A = 70$ °C	0.73	0.53
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ s	88	110
		Steady State	120	150
Maximum Junction-to-Foot (Drain)	R_{thJF}	65	80	°C/W

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

* Pb containing terminations are not RoHS compliant, exemptions may apply.



SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	-0.45		-0.8	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -9.6 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μA
		$V_{DS} = -9.6 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 70^\circ\text{C}$			-25	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 8 \text{ V}, V_{GS} = -4.5 \text{ V}$	-30			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5 \text{ V}, I_D = -4.6 \text{ A}$		0.024	0.030	Ω
		$V_{GS} = -2.5 \text{ V}, I_D = -3.8 \text{ A}$		0.031	0.040	
		$V_{GS} = -1.8 \text{ V}, I_D = -3.0 \text{ A}$		0.044	0.055	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -8 \text{ V}, I_D = -4.6 \text{ A}$		18		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.25 \text{ A}, V_{GS} = 0 \text{ V}$		-0.68	-1.1	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -6 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -4.6 \text{ A}$		16.5	25	nC
Gate-Source Charge	Q_{gs}		2			
Gate-Drain Charge	Q_{gd}		4.7			
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -6 \text{ V}, R_L = 6 \Omega$ $I_D \equiv -1.0 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_G = 6 \Omega$		20	40	ns
Rise Time	t_r		35	60		
Turn-Off Delay Time	$t_{d(off)}$		110	180		
Fall Time	t_f		90	150		
Source-Drain Reverse Recovery Time	t_{rr}		$I_F = -1.25 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$		100	

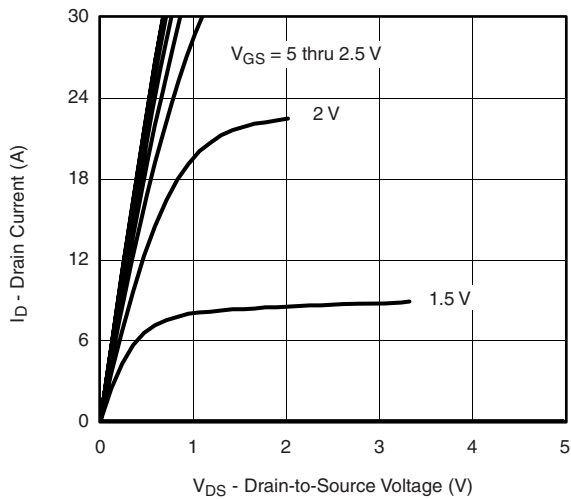
Notes:

a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.

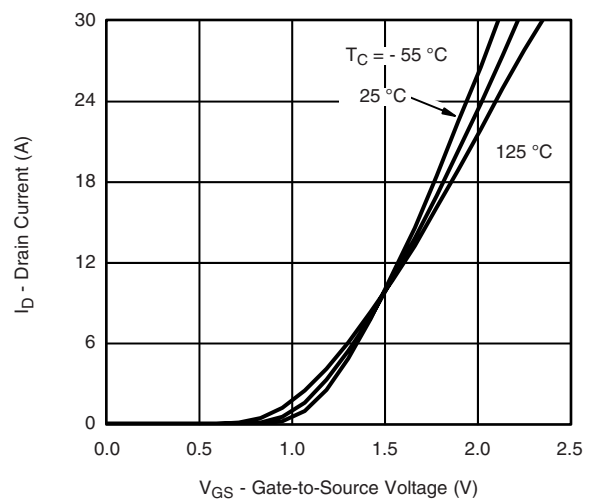
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25°C , unless otherwise noted

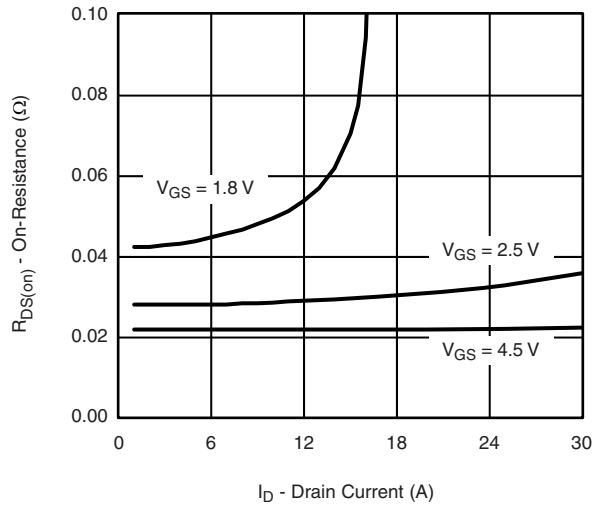


Output Characteristics

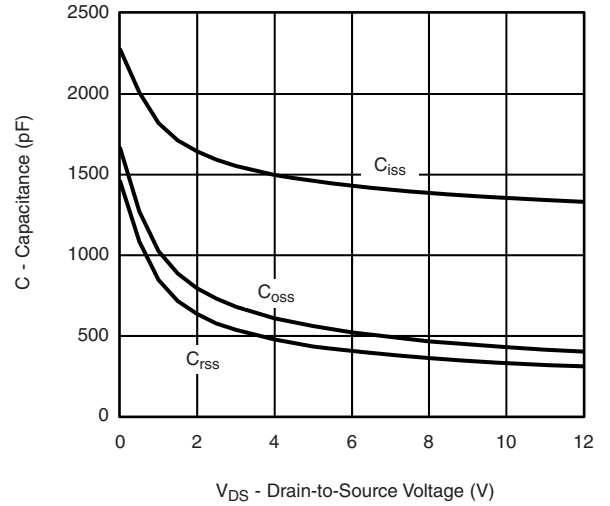


Transfer Characteristics

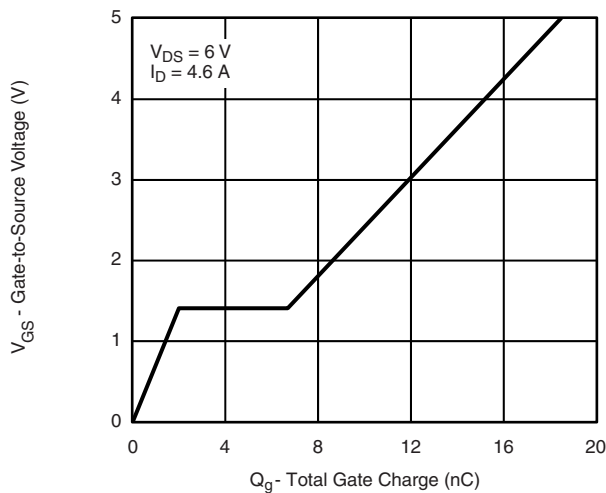
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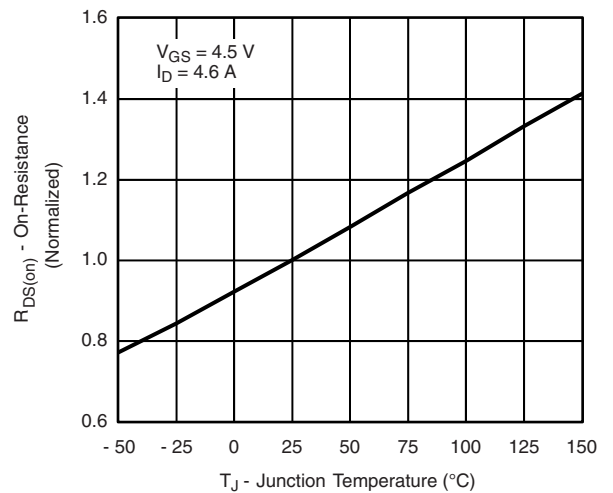
On-Resistance vs. Drain Current



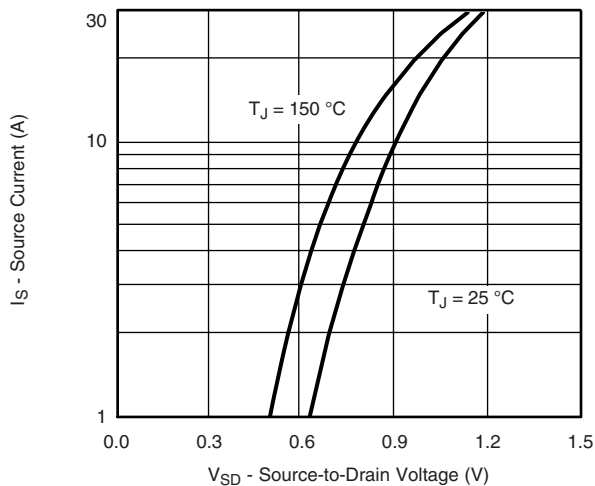
Capacitance



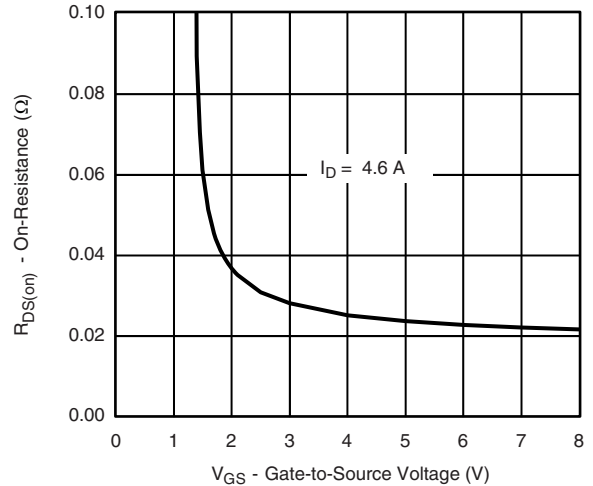
Gate Charge



On-Resistance vs. Junction Temperature

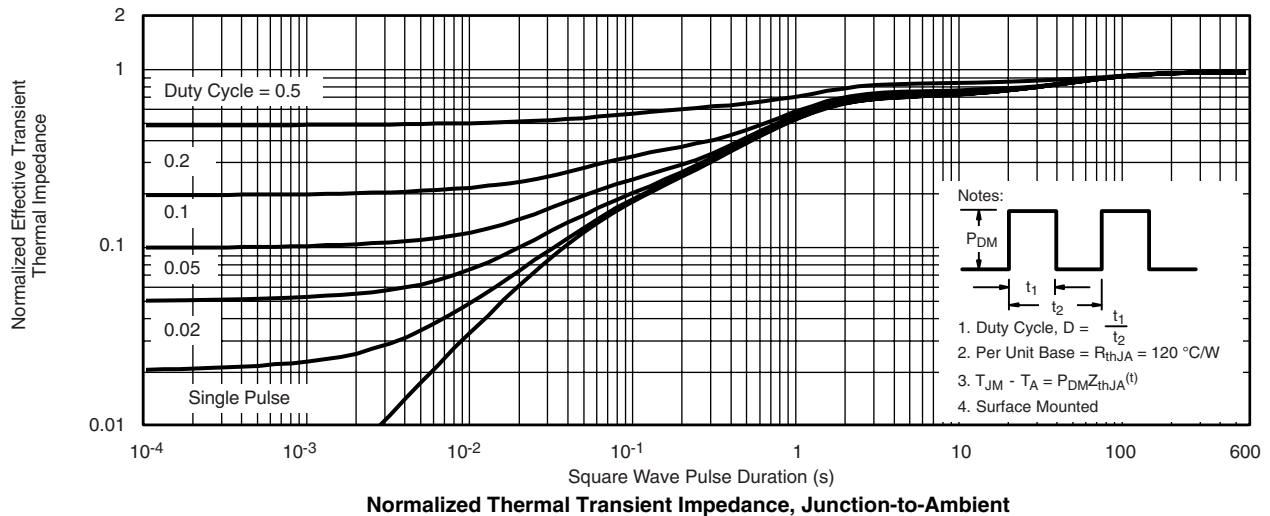
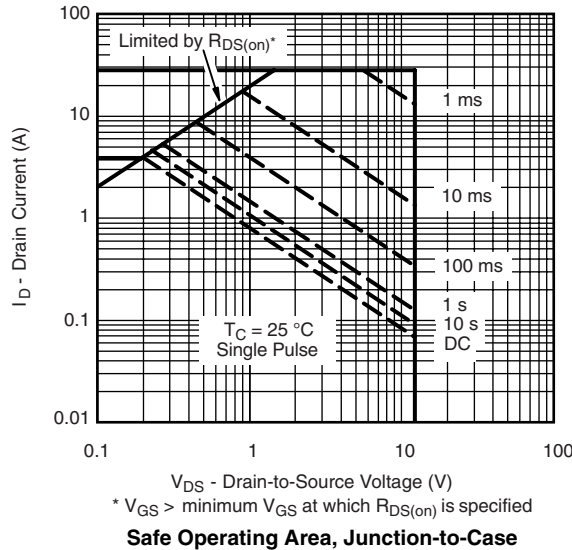
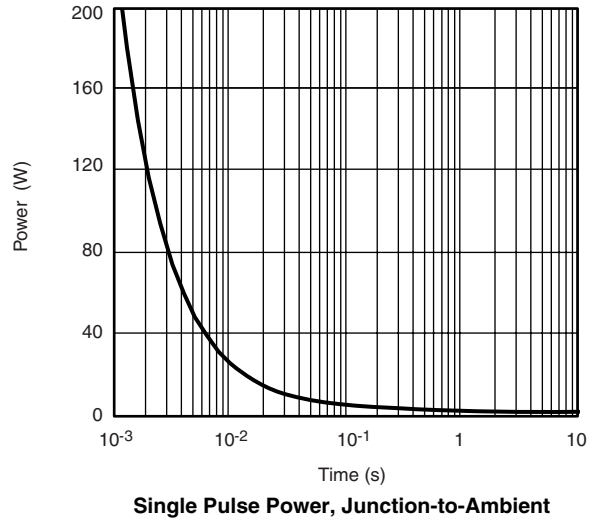
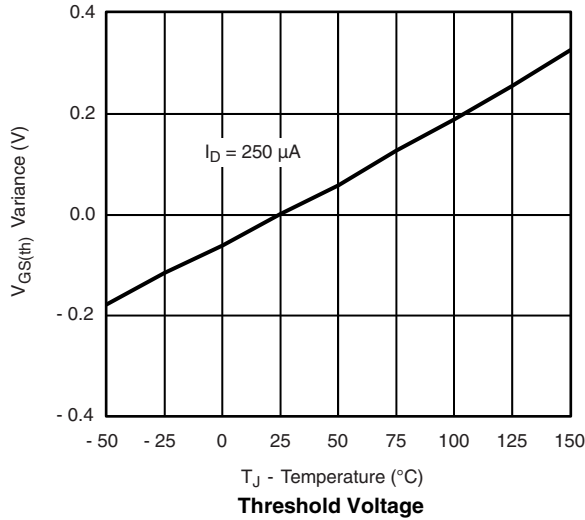


Source-Drain Diode Forward Voltage



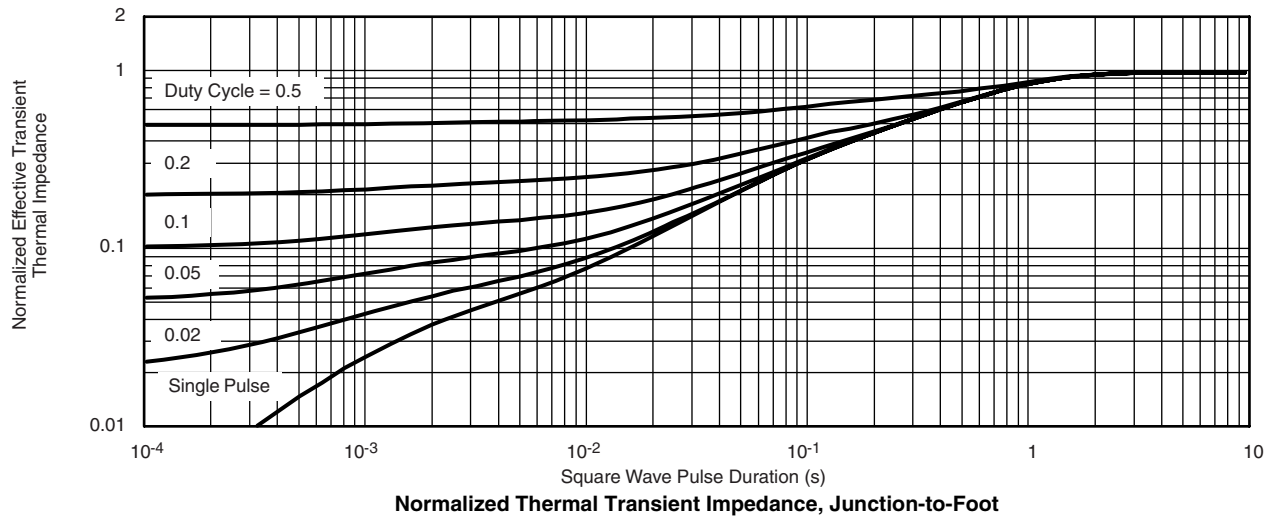
On-Resistance vs. Gate-to-Source Voltage

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